查询"2SK347的佛丽商Field Effect Transistor Silicon N-Channel MOS Type (π-MOS V)

2SK3472

Switching Regulator Applications

Unit: mm

• Low drain-source ON-resistance: RDS (ON) = $4.0 \text{ m}\Omega$ (typ.)

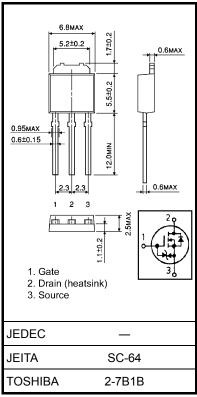
• High forward transfer admittance: $|Y_{fs}| = 0.8 S$ (typ.)

• Low leakage current: $I_{DSS} = 100 \,\mu\text{A}$ (max) ($V_{DS} = 450 \,\text{V}$)

• Enhancement model: $V_{th} = 2.0 \text{ to } 4.0 \text{ V (Vps} = 10 \text{ V, Ip} = 1 \text{ mA)}$

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	450	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	450	V
Gate-source voltage		V_{GSS}	±30	V
Drain current	DC (Note 1)	I _D	1	Α
	Pulse (Note 1)	I _{DP}	2	Α
Drain power dissipation	n (Tc = 25°C)	P _D	20	W
Single-pulse avalanche energy (Note 2)		E _{AS}	122	mJ
Avalanche current		I _{AR}	1	Α
Repetitive avalanche e	nergy (Note 3)	E _{AR}	2	mJ
Channel temperature		T _{ch}	150	°C
Storage temperature ra	ange	T _{stg}	-55 to150	°C



Weight: 0.36 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristic	Symbol	Max	Unit	
Thermal resistance, channel to case	R _{th (ch-c)}	6.25	°C/W	
Thermal resistance, channel to ambient	R _{th (ch-a)}	125	°C/W	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD} = 90~V,~T_{ch} = 25^{\circ}C$ (initial), L = 203 mH, R_G = 25 $\Omega,~I_{AR} = 1~A$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.



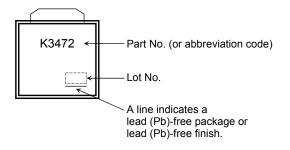
Energy (Ta = 25°C)

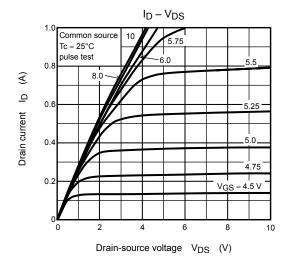
Char	acteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μΑ
Drain-source breakdown voltage		V (BR) GSS	$I_G = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$	±30	_	_	V
Drain cutoff current		I _{DSS}	V _{DS} = 450 V, V _{GS} = 0 V		_	100	μΑ
Drain-source brea	akdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	450	_	_	V
Gate threshold voltage		V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source ON-resistance		R _{DS} (ON)	V _{GS} = 10 V, I _D = 0.5 A		4.0	4.6	Ω
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 0.5 A	0.3	0.8	_	S
Input capacitance	•	C _{iss}			180	_	
Reverse transfer capacitance		C _{rss}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		2	_	pF
Output capacitance		C _{oss}			20	_	
Switching time	Rise time	t _r	V_{GS} 0 V V_{GS} 0 V $0 V$	_	7	_	ns
	Turn-on time	t _{on}		_	15	_	
	Fall time	t _f		_	30	_	
	Turn-off time	t _{off}		_	70	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	5		nC
Gate-source charge		Q _{gs}	$V_{DD} \simeq 360 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}$	_	3		
Gate-drain ("Miller") charge		Q _{gd}			2		

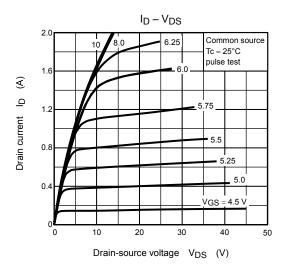
Source-Drain Ratings and Characteristics (Ta = 25°C)

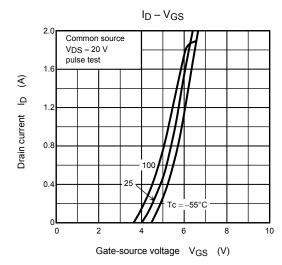
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	_	_	_	1	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	2	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 1 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	$I_{DR} = 1 \text{ A}, V_{GS} = 0 \text{ V},$	_	350	_	μS
Reverse recovery charge	Q _{rr}	dI _{DR} /dt = 100 A/μs	_	1.3	_	μС

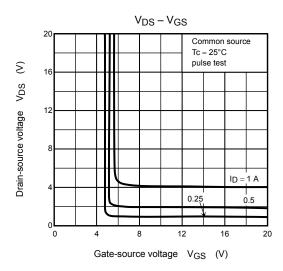
Marking

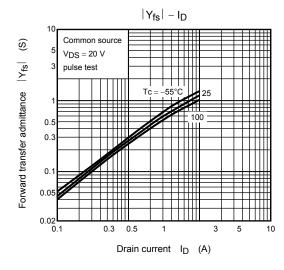


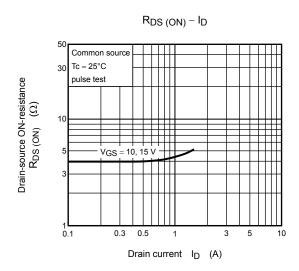




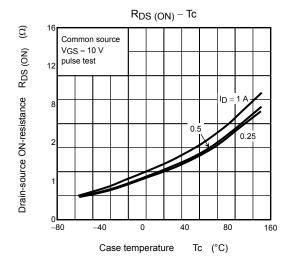


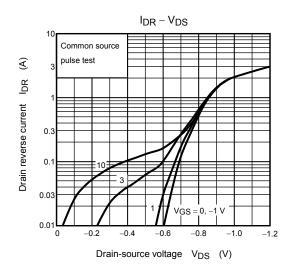


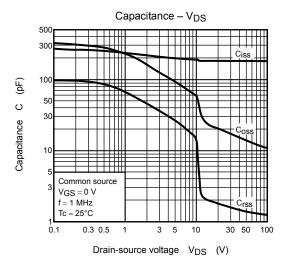


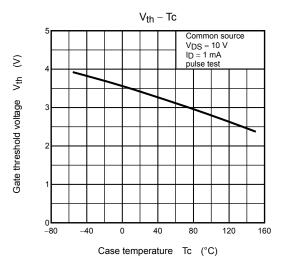


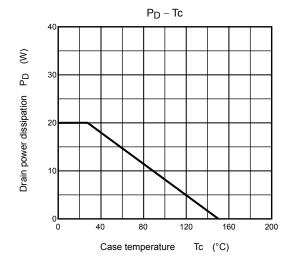
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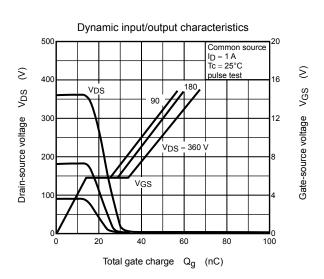


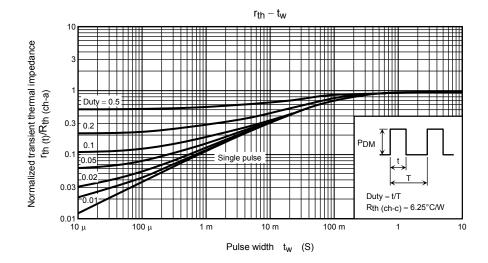


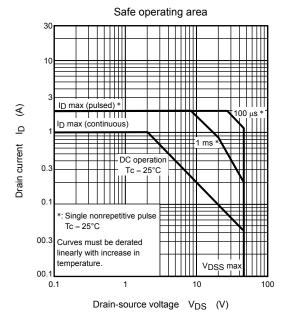


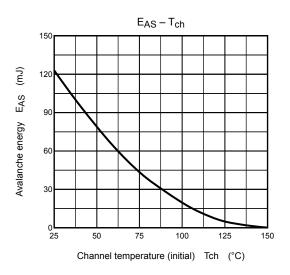


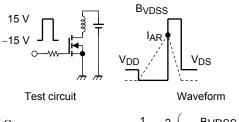












$$\begin{aligned} &R_G = 25~\Omega \\ &V_{DD} = 90~V,~L = 203~mH \end{aligned} \qquad E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - VDD} \right) \end{aligned}$$

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